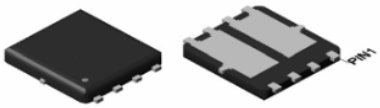
V_{DS}	30	V
$R_{DS(on),Typ}$ @ V_{GS}=10 V	17	mΩ
$R_{DS(on),Typ}$ @ V_{GS}=4.5 V	23	mΩ
I_D	30	A

Features

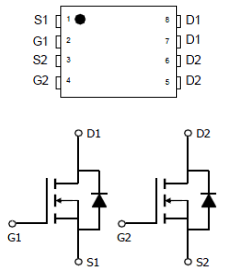
- Dual N-Channel，5V Logic Level Control
- Enhancement mode
- Low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

Pb-Free RoHS HF Halogen-Free

PDFN5x6



Top View



Part ID	Package Type	Marking	Tape and reel information
VSP018N03MD	PDFN5x6	018N03MD	3000pcs/reel

Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		30	V
I_D	Continuous drain current@V_{GS}=10V	T_C=25°C	30	A
		T_C=100°C	19	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	100	A
IAS	Avalanche current max	L=0.5mH	12	A
EAS	Avalanche energy, single pulsed ②		9	mJ
P_D	Maximum power dissipation	T_C=25°C	42	W
V_{GS}	Gate-Source voltage		±20	V
T_{STG}	Storage and operating temperature range		-55 to 175	°C

Thermal characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	55	°C/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3.5	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current (Tc=25℃)	V_{DS}=30V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current (Tc=125℃)	V_{DS}=30V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.0	1.5	2.2	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=10A	--	17	19	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=5A	--	23	28	mΩ
Dynamic Electrical Characteristics @ T_J= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=15V,V_{GS}=0V, f=1MHz	--	445	--	pF
C_{oss}	Output Capacitance		--	75	--	pF
C_{rss}	Reverse Transfer Capacitance		--	40	--	pF
Q_g	Total Gate Charge	V_{DS}=10V,I_D=10A, V_{GS}=10V	--	17	--	nC
Q_{gs}	GateSource Charge		--	2	--	nC
Q_{gd}	GateDrain Charge		--	6	--	nC
Switching Characteristics						
$t_{d(on)}$	Turnon Delay Time	V_{DD}=15V, I_D=6A, R_G=3.3Ω, V_{GS}=10V	--	6	--	nS
t_r	Turnon Rise Time		--	14	--	nS
$t_{d(off)}$	TurnOff Delay Time		-	21	--	nS
t_f	TurnOff Fall Time		--	10	--	nS
Source Drain Diode Characteristics						
I_{SD}	Sourcedrain current(Body Diode)	T_c=25℃	30	--	--	A
V_{SD}	Forward on voltage	T_j=25℃,I_{SD}=15A, V_{GS}=0V	--	0.91	1.3	V

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 6A, V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

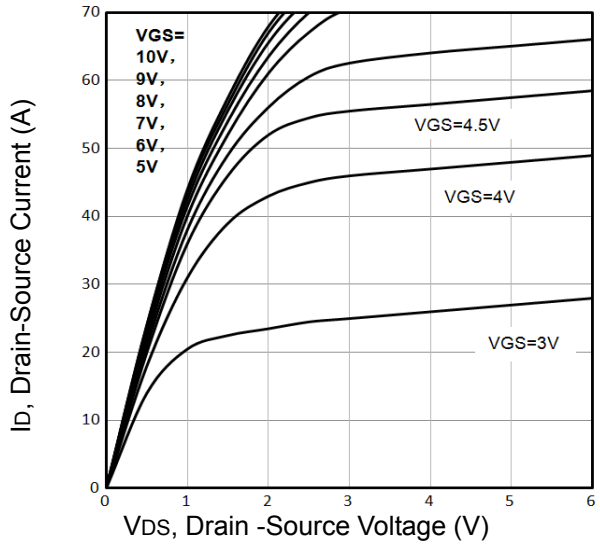


Fig1. Typical Output Characteristics

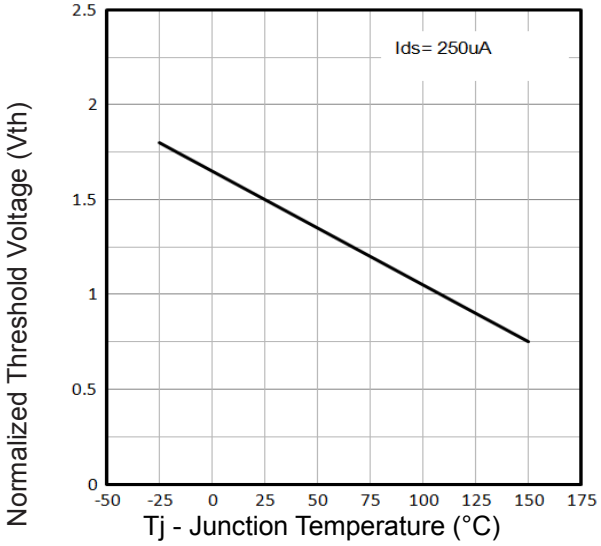


Fig2. Normalized Threshold Voltage Vs. Temperature

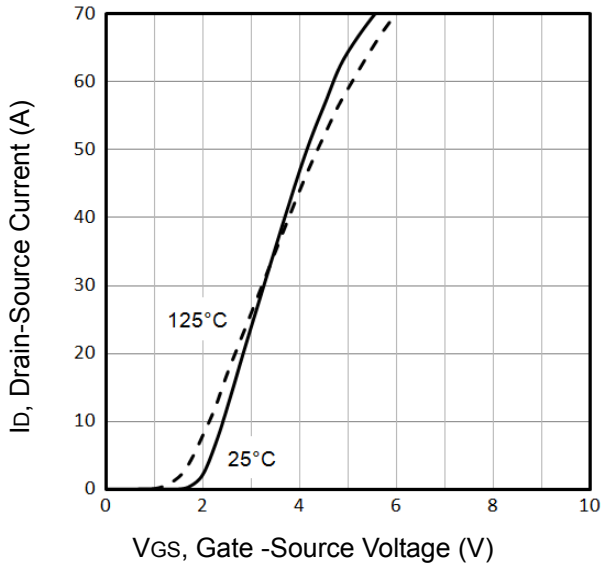


Fig3. Typical Transfer Characteristics

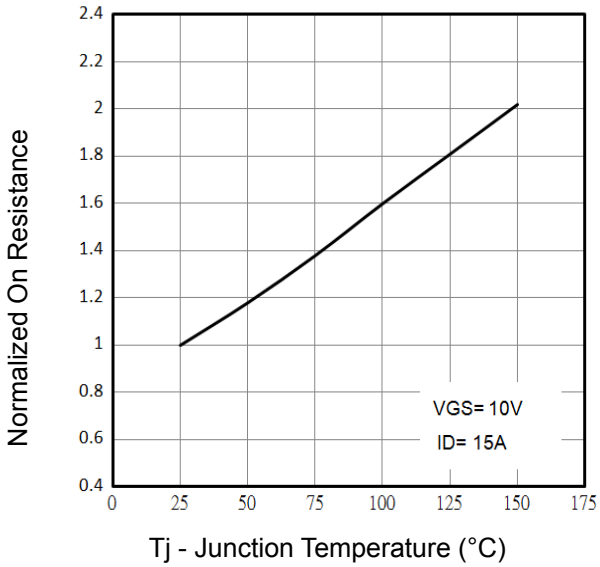


Fig4. Normalized On-Resistance Vs. Temperature

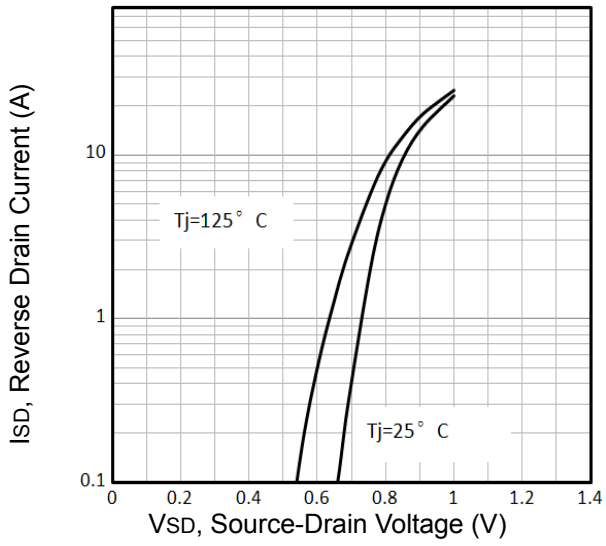


Fig5. Typical Source-Drain Diode Forward Voltage

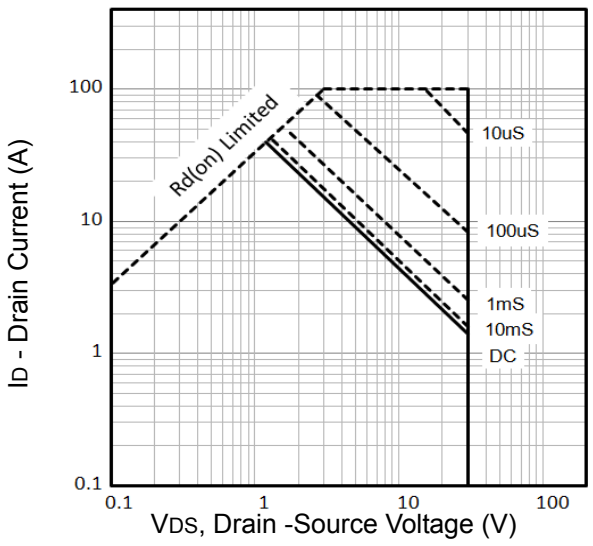


Fig6. Maximum Safe Operating Area

Typical Characteristics

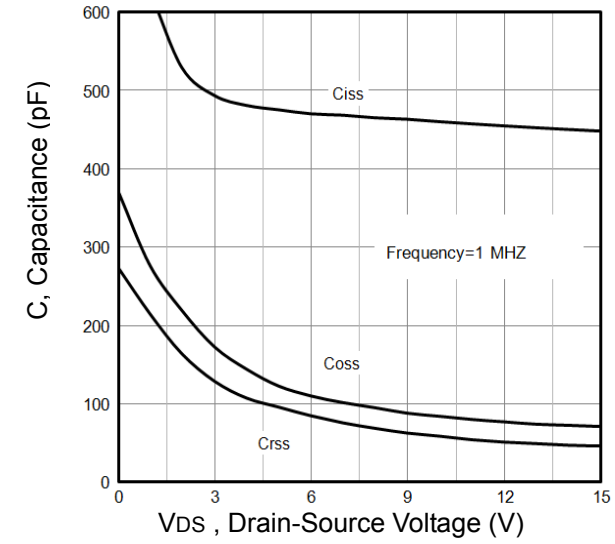


Fig7. Typical Capacitance Vs.Drain-Source Voltage

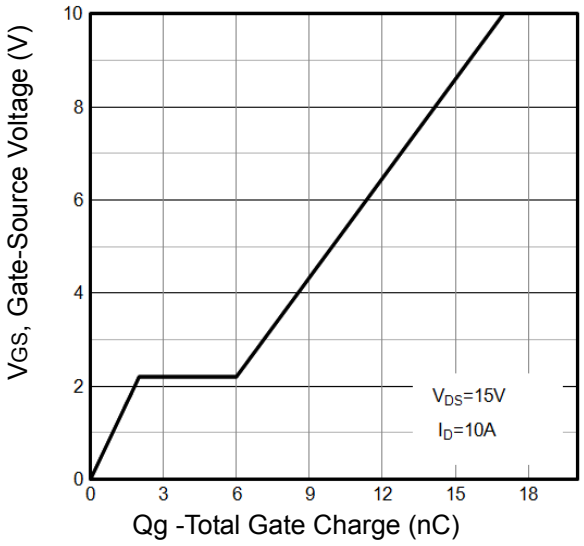


Fig8. Typical Gate Charge Vs.Gate-Source

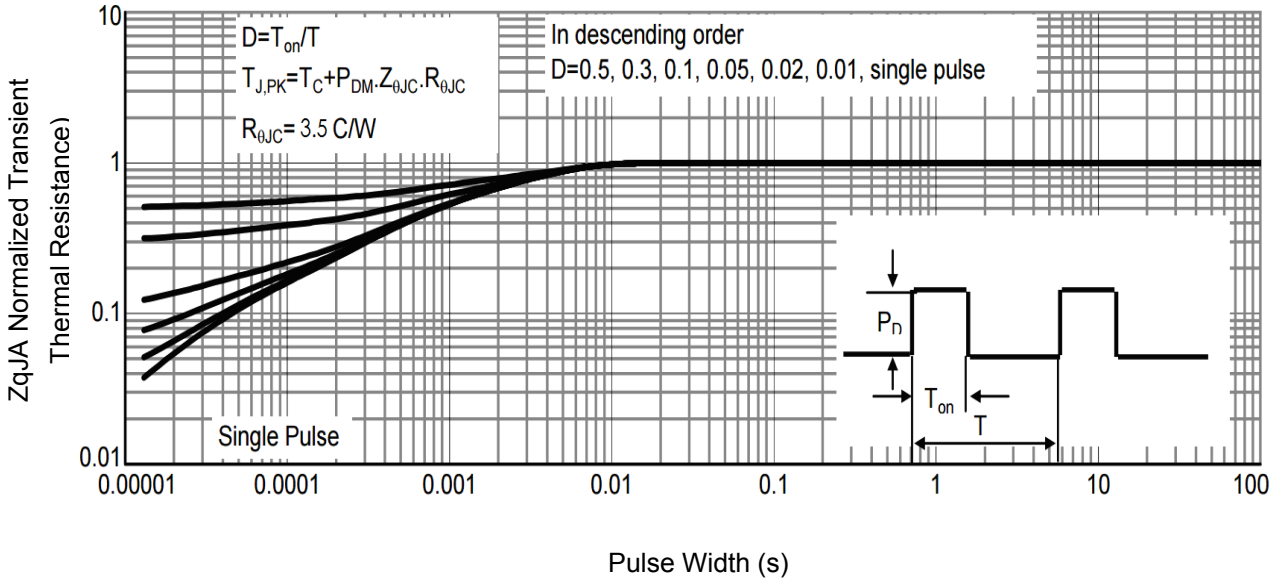


Fig 9 .Normalized Maximum Transient Thermal Impedance

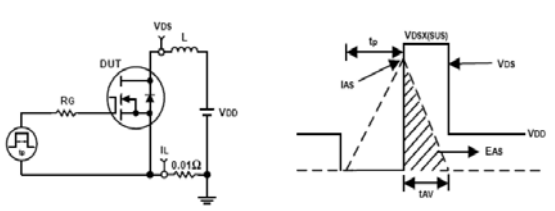


Fig10. Unclamped Inductive Test Circuit and waveforms

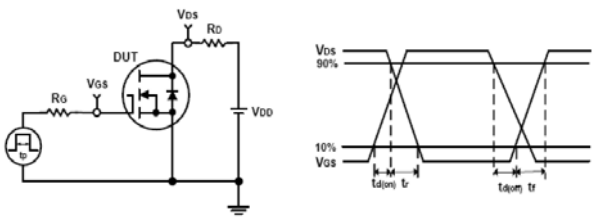
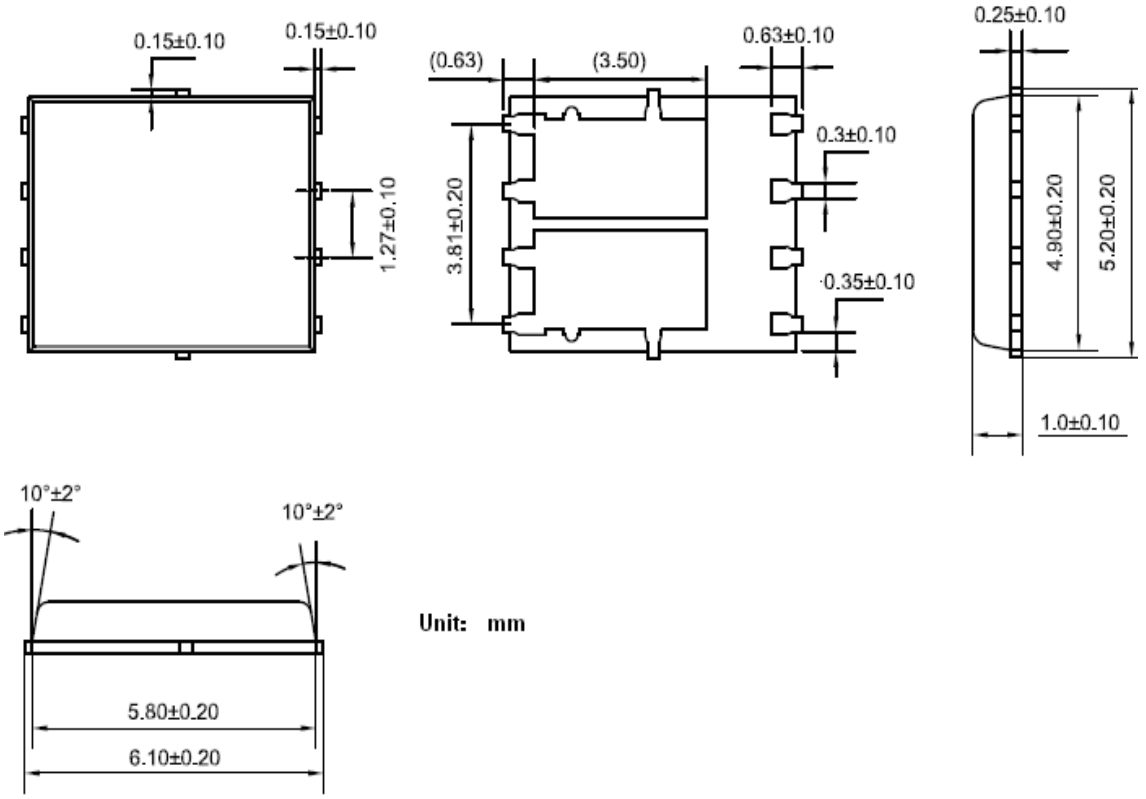


Fig11. Switching Time Test Circuit and waveforms

DFN5x6 Package Outline Data



Unit: mm

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